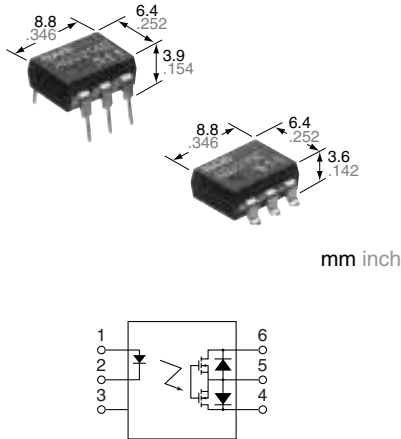


<h1 style="margin: 0;">Panasonic</h1> <p style="margin: 0;">ideas for life</p>	<p><b>General use and economy type.</b>  <b>DIP (1 Form A) 6-pin type.</b>  <b>Reinforced insulation</b>  <b>5,000V type.</b></p>	<h1 style="margin: 0;">GU-E PhotoMOS</h1> <p style="margin: 0;">(AQV210E, AQV210EH)</p>
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## FEATURES



- 1. Controls low-level analog signals**  
PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.
- 2. Control with low-level input signals**
- 3. Controls various types of loads such as relays, motors, lamps and solenoids.**
- 4. Optical coupling for extremely high isolation**  
Unlike mechanical relays, the PhotoMOS relay combines LED and optoelectronic device to transfer signals using light for extremely high isolation.
- 5. Eliminates the need for a counter electromotive force protection diode in the drive circuits on the input side**

- 6. Stable on resistance**
- 7. Low-level off state leakage current**
- 8. Eliminates the need for a power supply to drive the power MOSFET**  
A power supply used to drive the power MOSFET is unnecessary because of the built-in optoelectronic device. This results in easy circuit design and small PC board area.
- 9. Low thermal electromotive force (Approx. 1 μV)**

## TYPICAL APPLICATIONS

- High-speed inspection machines
- Telephone equipment
- Data communication equipment
- Computer

## TYPES

Type	I/O isolation	Output rating*		Part No.				Packing quantity	
				Through hole terminal	Surface-mount terminal				
				Load voltage	Load current	Tube packing style		Tape and reel packing style	
AC/DC	Standard 1,500 V AC	350 V	130 mA	AQV210E	AQV210EA	AQV210EAX	AQV210EAZ	1 tube contains 50 pcs. 1 batch contains 500 pcs.	1,000 pcs.
		400 V	120 mA	AQV214E	AQV214EA	AQV214EAX	AQV214EAZ		
	Reinforced 5,000 V	350 V	130 mA	AQV210EH	AQV210EHA	AQV210EHAX	AQV210EHAZ		
		400 V	120 mA	AQV214EH	AQV214EHA	AQV214EHAX	AQV214EHAZ		

\*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

## RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Sym- bol	Type of connec- tion	AQV210E(A)	AQV214E(A)	AQV210EH(A)	AQV214EH(A)	Remarks	
Input	LED forward current	I <sub>F</sub>		50 mA					
	LED reverse voltage	V <sub>R</sub>		5 V					
	Peak forward current	I <sub>FP</sub>		1 A				f = 100 Hz, Duty factor = 0.1%	
	Power dissipation	P <sub>in</sub>		75 mW					
Output	Load voltage (peak AC)	V <sub>L</sub>		350 V	400 V	350 V	400 V		
	Continuous load current	I <sub>L</sub>		A	0.13 A	0.12 A	0.13 A	0.12 A	A connection: Peak AC, DC; B, C connection: DC
				B	0.15 A	0.13 A	0.15 A	0.13 A	
				C	0.17 A	0.15 A	0.17 A	0.15 A	
	Peak load current	I <sub>peak</sub>		0.4 A	0.3 A	0.4 A	0.3 A	A connection: 100 ms (1 shot), V <sub>L</sub> =DC	
Power dissipation	P <sub>out</sub>	500 mW							
Total power dissipation		P <sub>T</sub>	550 mW						
I/O isolation voltage		V <sub>iso</sub>	1,500 V AC		5,000 V AC				
Temperature limits	Operating	T <sub>opr</sub>	-40°C to +85°C -40°F to +185°F				Non-condensing at low temp.		
	Storage	T <sub>stg</sub>	-40°C to +100°C -40°F to +212°F						

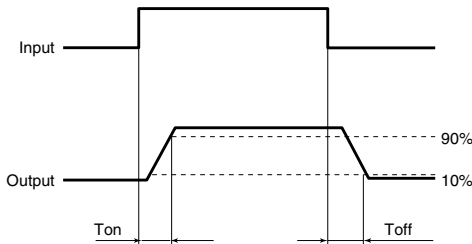
# GU-E PhotoMOS (AQV210E, AQV210EH)

## 2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item		Symbol	Type of connection	AQV210E(A)	AQV214E(A)	AQV210EH(A)	AQV214EH(A)	Condition	
Input	LED operate current	Typical	I <sub>Fon</sub>	1.1 mA		1.6 mA		I <sub>L</sub> = Max.	
		Maximum		3 mA					
	LED turn off current	Minimum	I <sub>Foff</sub>	0.3 mA		0.4 mA		I <sub>L</sub> = Max.	
		Typical		1.0 mA		1.5 mA			
LED dropout voltage	Typical	V <sub>F</sub>	—	1.25 V (1.14 V at I <sub>F</sub> = 5 mA)				I <sub>F</sub> = 50 mA	
	Maximum			1.5 V					
Output	On resistance	Typical	R <sub>on</sub>	A	23 Ω	30 Ω	23 Ω	30 Ω	I <sub>F</sub> = 5 mA I <sub>L</sub> = Max. Within 1 s on time
		Maximum			35 Ω	50 Ω	35 Ω	50 Ω	
		Typical	R <sub>on</sub>	B	11.5 Ω	22.5 Ω	11.5 Ω	22.5 Ω	I <sub>F</sub> = 5 mA I <sub>L</sub> = Max. Within 1 s on time
		Maximum			17.5 Ω	25 Ω	17.5 Ω	25 Ω	
	Typical	R <sub>on</sub>	C	6.0 Ω	11.3 Ω	6.0 Ω	11.3 Ω	I <sub>F</sub> = 5 mA I <sub>L</sub> = Max. Within 1 s on time	
	Maximum			8.8 Ω	12.5 Ω	8.8 Ω	12.5 Ω		
Output capacitance	Typical	C <sub>out</sub>	A	45 pF				I <sub>F</sub> = 0 mA V <sub>B</sub> = 0 V f = 1 MHz	
Off state leakage current	Maximum	—	—	1 μA				I <sub>F</sub> = 0 mA V <sub>L</sub> = Max.	
Transfer characteristics	Switching speed	Turn on time*	T <sub>on</sub>	—	0.5 ms		0.7 ms		I <sub>F</sub> = 0 mA → 5 mA** I <sub>L</sub> = Max.
					Turn off time*	T <sub>off</sub>	—	0.05 ms	
		I/O capacitance	Typical	C <sub>iso</sub>				—	0.8 pF
			Maximum		1.5 pF				
	Initial I/O isolation resistance	Minimum	R <sub>iso</sub>	—	1,000 MΩ				500 V DC

\*Turn on/Turn off time

For type of connection



\*\* Recommendable LED forward current

Standard type: 5 mA

Reinforced type: 5 to 10 mA

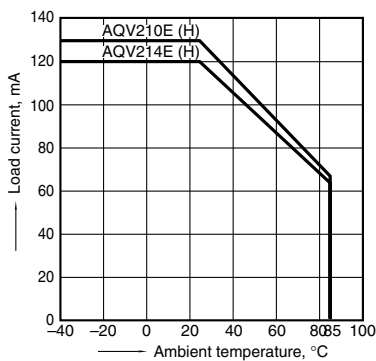
- For Dimensions
- For Schematic and Wiring Diagrams
- For Cautions for Use

## REFERENCE DATA

### 1. Load current vs. ambient temperature characteristics

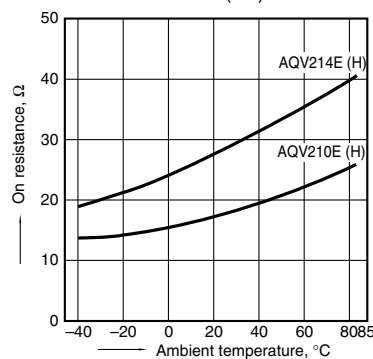
Allowable ambient temperature: -40°C to +85°C  
-40°F to +185°F

Type of connection: A



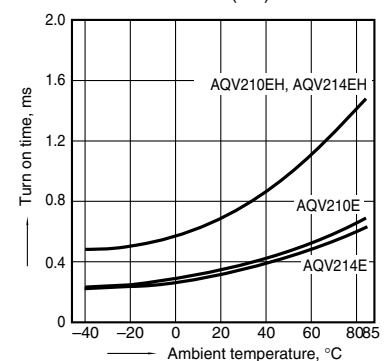
### 2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 4 and 6;  
LED current: 5 mA; Load voltage: Max. (DC);  
Continuous load current: Max. (DC)



### 3. Turn on time vs. ambient temperature characteristics

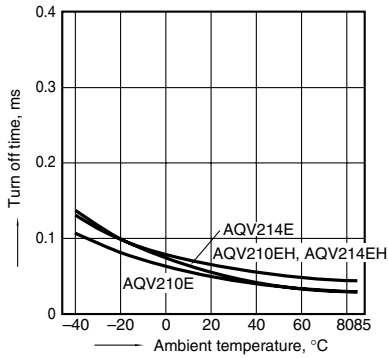
LED current: 5 mA;  
Load voltage: Max. (DC);  
Continuous load current: Max. (DC)



# GU-E PhotoMOS (AQV210E, AQV210EH)

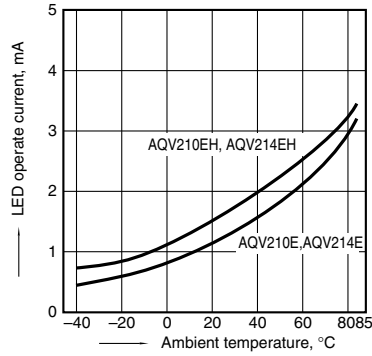
## 4. Turn off time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC); Continuous load current: Max. (DC)



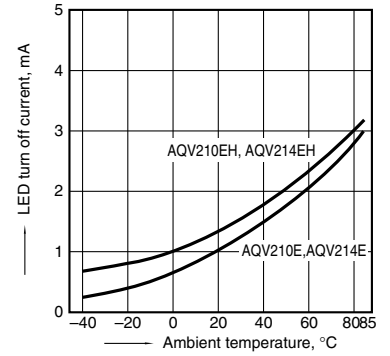
## 5. LED operate current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



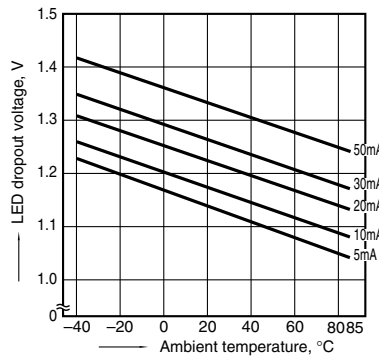
## 6. LED turn off current vs. ambient temperature characteristics

Load voltage: Max. (DC); Continuous load current: Max. (DC)



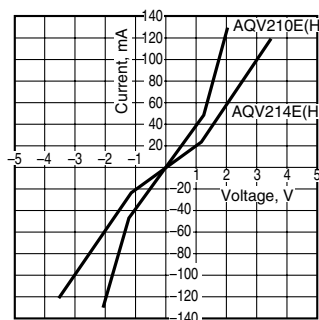
## 7. LED dropout voltage vs. ambient temperature characteristics

Sample: All types  
LED current: 5 to 50 mA



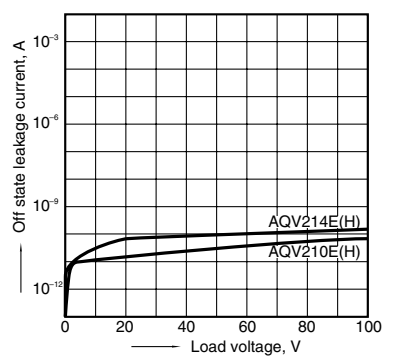
## 8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 4 and 6;  
Ambient temperature: 25°C 77°F



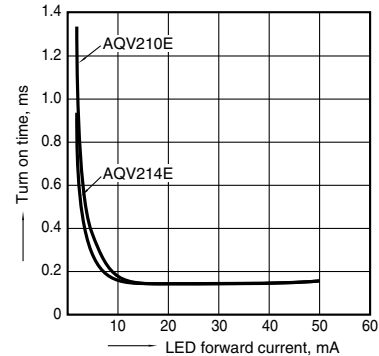
## 9. Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 4 and 6;  
Ambient temperature: 25°C 77°F



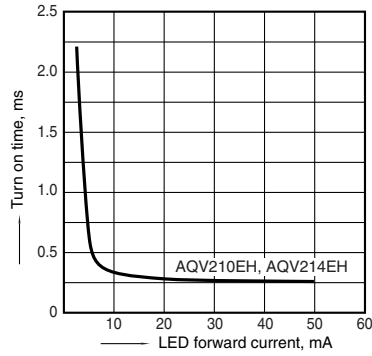
## 10-(1). Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;  
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



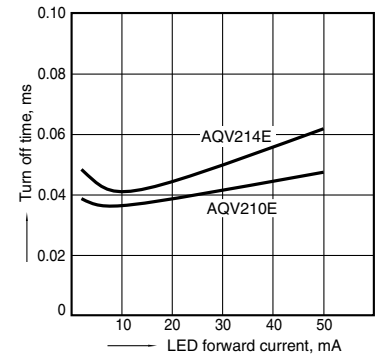
## 10-(2). Turn on time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;  
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



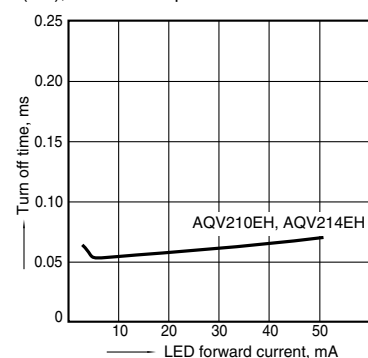
## 11-(1). Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;  
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



## 11-(2). Turn off time vs. LED forward current characteristics

Measured portion: between terminals 4 and 6;  
Load voltage: Max. (DC); Continuous load current: Max. (DC); Ambient temperature: 25°C 77°F



## 12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 4 and 6;  
Frequency: 1 MHz;  
Ambient temperature: 25°C 77°F

